SILICON TRANSISTOR
2SB1261-Z

PNP SILICON EPITAXIAL TRANSISTOR
MP-3

DESCRIPTION

2SB1261-Z is designed for Audio Frequency Amplifier and Switching, especially in Hybrid Integrated Circuits.

FEATURES

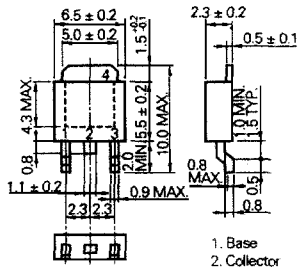
- High h_{FE} h_{FE} = 100 to 400
- Low $V_{CE(sat)}$ $V_{CE(sat)} \leqq 0.3$ V

QUALITY GRADE

Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

PACKAGE DIMENSIONS
(in millimeters)



ABSOLUTE MAXIMUM RATINGS (T_a = 25 °C)

Collector to Base Voltage	V_{CBO}	−60	V
Collector to Emitter Voltage	V_{CEO}	−60	V
Emitter to Base Voltage	V_{EBO}	−7.0	V
Collector Current (DC)	I_C	−3.0	A
Collector Current (Pulse)	I_C*	−5.0	A
Base Current (DC)	I_B	−0.5	A
Total Power Dissipation (T_a = 25 °C)	P_{T1}**	2.0	W
Total Power Dissipation (T_C = 25 °C)	P_{T2}	10	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	−55 to +150	°C

* PW ≦ 10 ms, Duty Cycle ≦ 50 %

** When mounted on ceramic substrate of 7.5 cm² × 0.7 mm

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ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	I_{CBO}			−10	μA	V_{CB} = −60 V, I_E = 0
Emitter Cutoff Current	I_{EBO}			−10	μA	V_{EB} = −7.0 V, I_C = 0
DC Current Gain	h_{FE1}*	60				V_{CE} = −2.0 V, I_C = −0.2 A
DC Current Gain	h_{FE2}*	100		400		V_{CE} = −2.0 V, I_C = −0.6 A
DC Current Gain	h_{FE3}*	50				V_{CE} = −2.0 V, I_C = −2.0 A
Collector Saturation Voltage	$V_{CE(sat)}$*		−0.2	−0.3	V	I_C = −1.5 A, I_B = −0.15 A
Base Saturation Voltage	$V_{BE(sat)}$*		−0.94	−1.2	V	I_C = −1.5 A, I_B = −0.15 A
Gain Bandwidth Product	f_T		50		MHz	V_{CE} = −5.0 V, I_E = 1.5 A
Output Capacitance	C_{ob}		40		pF	V_{CB} = −10 V, I_E = 0, f = 1.0 MHz
Turn-on Time	t_{on}		0.15	0.5	μs	I_C = −1.0 A, V_{CC} = −10 V, R_L = 10 Ω, I_{B1} = $-I_{B2}$ = −0.1 A
Storage Time	t_{stg}		0.5	2.0	μs	
Fall time	t_f		0.1	0.5	μs	

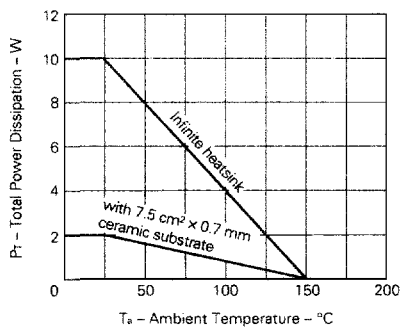
* Pulsed: PW ≦ 350 μs, Duty Cycle ≦ 2 %

h_{FE} Classification

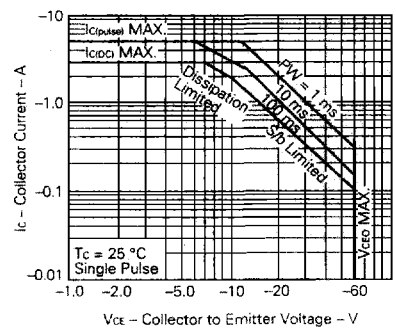
MARKING	M	L	K
h_{FE2}	100 to 200	160 to 320	200 to 400

TYPICAL CHARACTERISTICS (T_a = 25 °C)

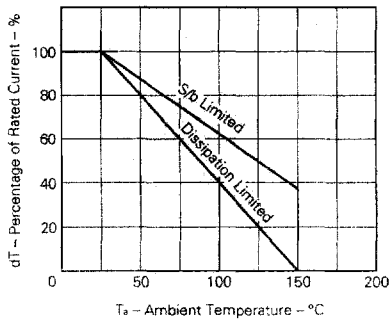
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



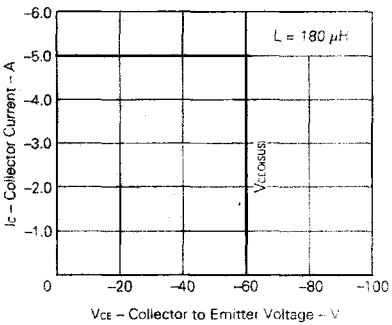
FORWARD BIAS SAFE OPERATING AREA



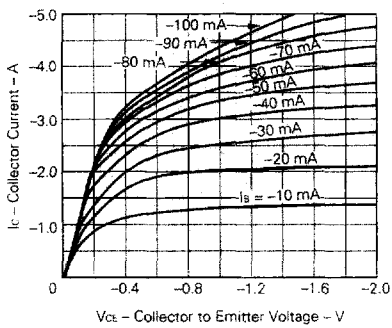
DERATING CURVE OF SAFE OPERATING AREA



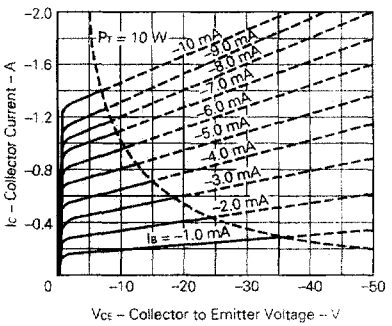
RESERVE BIAS SAFE OPERAING AREA



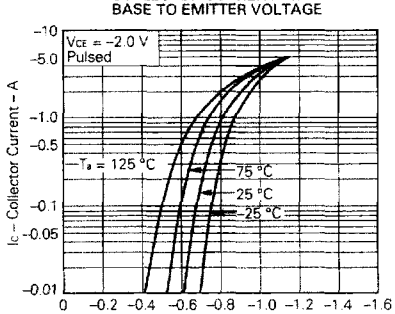
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



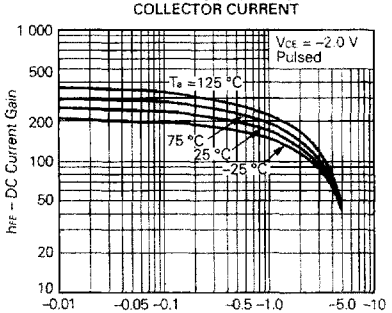
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



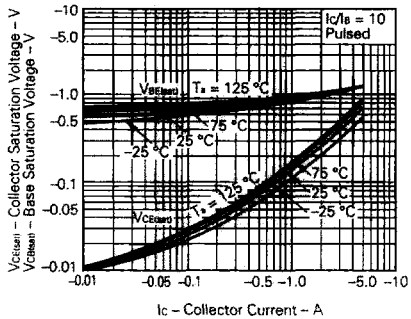
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



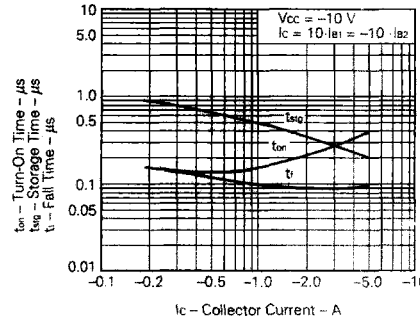
DC CURRENT GAIN vs. COLLECTOR CURRENT



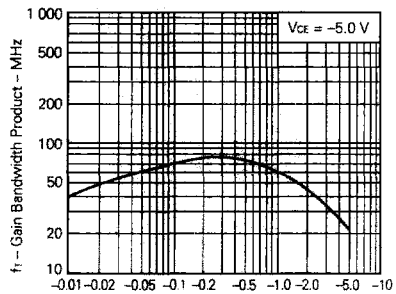
BASE AND COLLECTOR SATURATION VOLTAGE vs. COLLECTOR CURRENT



FALL, STORAGE AND TURN-ON TIME vs. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT



OUTPUT CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE